ISO/TC22/SC32/WG3 N 3289

ISO/draft for FDIS 11452-3

ISO/TC 22/SC 32

Secretariat: JISC

Date 2023-09-12: 2024-02-21

# Road vehicles — Component test methods for electrical disturbances from narrowband radiated electromagnetic energy—<u>—</u>

# Part 3: Transverse electromagnetic (TEM) cell

Partie 3: Cellule électromagnétique transverse (TEM)

ISO/EDIS 11/52 3

https://standards.iteh.ai/catalog/standards/iso/64ae42e2-d5c4-49dd-a0b2-d081ef66b8de/iso-fdis-11452-3

FDIS stage

#### © ISO 2024

All rights reserved. Unless otherwise specified, or required in the context of its implementation, no part of this publication may be reproduced or utilized otherwise in any form or by any means, electronic or mechanical, including photocopying, or posting on the internet or an intranet, without prior written permission. Permission can be requested from either ISO at the address below or ISO's member body in the country of the requester.

ISO copyright office CP 401 • Ch. de Blandonnet 8 CH-1214 Vernier, Geneva Phone: + 41 22 749 01 11 E-mail: copyright@iso.org

Published in Switzerland

Website: www.iso.org

## iTeh Standards (https://standards.iteh.ai) Document Preview

ISO/FDIS 11452-3

https://standards.iteh.ai/catalog/standards/iso/64ae42e2-d5c4-49dd-a0b2-d081ef66b8de/iso-fdis-11452-3

### **Contents**—Page

Forev	vord	v
Introd	duction	vi
1	Scope	1
2	Normative references	1
3	Terms and definitions	1
4	Test conditions	1
5	Test apparatus	2
5.1	TEM cell	2
5.2	Instrumentation	3
5.3	Test set-up	5
5.3.1	General	5
5.3.2	Exposure of device under test and wiring harness (for major field coupling to the harness)	5
5.3.3	Exposure of device under test alone (for major field coupling to that device)	8
6	Test procedure	10
6.1	Test plan	
6.2	Test method	10
6.2.1	General	
6.2.2	Test level setting	10
6.2.3	DUT test	11
6.3	Test report	12
	x A (informative) TEM cell dimensions ISO TDIS 11452-3	
Annex B (informative) Calculations and measurements of TEM-cell frequency range		16
B.1	General	
B.2	Method 1	16
B.3	Method 2	16
Annex	x C (informative) Installation of external components and low pass filter design	18
C.1	Connector panel	18
C.2	External components and low pass filter	18
C.3	Design rules for the low pass filter	19
C.3.1	General	19
C.3.2	Lower cut-off frequency	20
C.3.3	Useful frequency range	20
C.3.4	Upper cut-off frequency	20
Annex	x D (informative) Test setup without low pass filters	21
D.1	General	21
D.2	Test set-up	21
Annes	x E (informative) Function performance status classification (FPSC) and test severity levels	26

E.1	General	.26
E.2	Classification of test severity levels	. 26
E.3	Example of FPSC application using test severity levels	. 26
Biblios	Bibliography	

## iTeh Standards (https://standards.iteh.ai) Document Preview

ISO/FDIS 11452-3

https://standards.iteh.ai/catalog/standards/iso/64ae42e2-d5c4-49dd-a0b2-d081ef66b8de/iso-fdis-11452-3

#### **Foreword**

ISO (the International Organization for Standardization) is a worldwide federation of national standards bodies (ISO member bodies). The work of preparing International Standards is normally carried out through ISO technical committees. Each member body interested in a subject for which a technical committee has been established has the right to be represented on that committee. International organizations, governmental and non-governmental, in liaison with ISO, also take part in the work. ISO collaborates closely with the International Electrotechnical Commission (IEC) on all matters of electrotechnical standardization.

The procedures used to develop this document and those intended for its further maintenance are described in the ISO/IEC Directives, Part 1. In particular, the different approval criteria needed for the different types of ISO documents should be noted. This document was drafted in accordance with the editorial rules of the ISO/IEC Directives, Part 2 (see <a href="www.iso.org/directives">www.iso.org/directives</a>).

Attention is drawnISO draws attention to the possibility that some of the elementsimplementation of this document may beinvolve the subjectuse of (a) patent(s). ISO takes no position concerning the evidence, validity or applicability of any claimed patent rights in respect thereof. As of the date of publication of this document, ISO had not received notice of (a) patent(s) which may be required to implement this document. However, implementers are cautioned that this may not represent the latest information, which may be obtained from the patent database available at www.iso.org/patents. ISO shall not be held responsible for identifying any or all such patent rights. Details of any patent rights identified during the development of the document will be in the Introduction and/or on the ISO list of patent declarations received (see ).

Any trade name used in this document is information given for the convenience of users and does not constitute an endorsement.

For an explanation on of the voluntary nature of standards, the meaning of ISO specific terms and expressions related to conformity assessment, as well as information about ISO's adherence to the World Trade Organization (WTO) principles in the Technical Barriers to Trade (TBT), see the following URL: www.iso.org/iso/foreword.html.

The committee responsible for this This document is was prepared by Technical Committee ISO/TC 22, Road vehicles, Subcommittee SC 32, Electrical and electronic components and general system aspects.

This thirdfourth edition cancels and replaces the secondthird edition (ISO 11452-3:2001),2016), of which has been technically revised with the followingit constitutes a minor revision. The changes:

the use of forward power <u>are</u> as the levelling parameter to make it consistent with the other <u>ISO 11452 standards has been implemented; follows:</u>

——Formula (1) Annex D for testing of devices without using low pass filters has been included.

— in 6.6.2 was modified.

A list of all parts in the ISO 11452 series can be found on the ISO website.

Any feedback or questions on this document should be directed to the user's national standards body. A complete listing of these bodies can be found at www.iso.org/members.html.

#### Introduction

Immunity measurements of complete road vehicles are generally able to be carried out only by the vehicle manufacturer, owing to, for example, high costs of absorber-lined shielded enclosures, the desire to preserve the secrecy of prototypes or a large number of different vehicle models.

For research, development and quality control, a laboratory measuring method can be used by both vehicle manufacturers and equipment suppliers to test electronic components.

The TEM cell method has the major advantage of not radiating energy into the surrounding environment. The method can be used for testing either the immunity of a component with the field coupling to the wiring harness or the immunity of the component alone with minimum exposure to the wiring harness.

# iTeh Standards (https://standards.iteh.ai) Document Preview

ISO/FDIS 11452-3

https://standards.iteh.ai/catalog/standards/iso/64ae42e2-d5c4-49dd-a0b2-d081ef66b8de/iso-fdis-11452-3

### <u>Road vehicles — Component test methods for electrical disturbances</u> <u>from narrowband radiated electromagnetic energy —</u>

#### Part 3:

### Transverse electromagnetic (TEM) cell

#### 1 Scope

This document specifies transverse electromagnetic (TEM) cell tests for determining the immunity of electronic components of passenger cars and commercial vehicles to electrical disturbances from narrowband radiated electromagnetic energy, regardless of the vehicle propulsion system (e.g. spark-ignition engine, diesel engine, electric motor).

The electromagnetic disturbances considered are limited to continuous narrowband electromagnetic fields.

#### 2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

ISO 11452-1, Road vehicles — Component test methods for electrical disturbances from narrowband radiated electromagnetic energy — Part 1: General principles and terminology

### 3 Terms and definitions tps://standards.iteh.ai)

For the purposes of this document, the terms and definitions given in ISO 11452-1 apply.

ISO and IEC maintain terminological terminology databases for use in standardization at the following addresses:

- — IEC Electropedia: available at
- ——ISO Online browsing platform: available at <a href="https://www.iso.org/obp">https://www.iso.org/obp</a>
- IEC Electropedia: available at https://www.electropedia.org/

#### 4 Test conditions

The upper frequency range limit of the TEM cell is a direct function of the TEM cell dimensions.

For testing automotive electronic systems, a 0,01 MHz to 200 MHz TEM cell should be used. See <u>Annex A Annex A for suggested cell dimensions. See Annex B for methods to determine TEM-cell frequency range</u>.

The user shall specify the test severity level or levels over the frequency range. See Annex EAnnex E for suggested test severity levels.

Standard test conditions shall be those given in ISO 11452-1 for the following:

- test temperature;
- supply voltage;
- —modulation:

#### ISO/TC22/SC32/WG3FDIS 11452-3:2024(en)

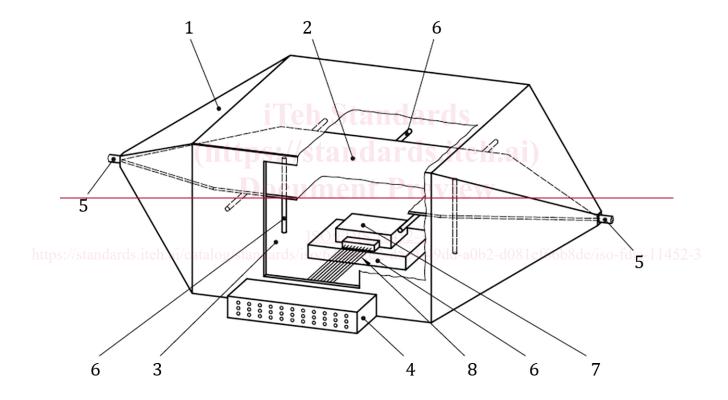
- dwell time;
- frequency step sizes;
- definition of test severity levels;
- test-signal quality.

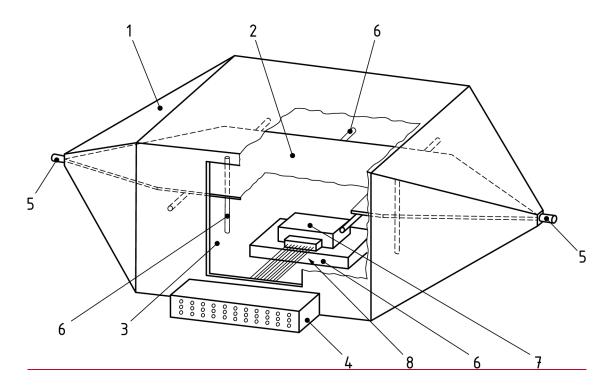
#### 5 Test apparatus

#### 5.1 TEM cell

The TEM cell used for this test is a rectangular coaxial line with a  $50 \Omega$  characteristic impedance (see Figure 1). The device under test is exposed to a uniform TEM field.

The TEM cell is a laboratory measurement system which can be used to generate test fields within 2 dB of the theoretical value if the device under test does not occupy an excessive portion of the test volume (see <u>5.3</u><del>5.3</del>).





#### Key

- 1 outer conductor (shield)
- 2 septum (inner conductor)
- 3 access door
- 4 connector panel (optional) (1777) (1778) (1778) (1778) (1778)
- 5 coaxial connectors
- 6 dielectric support (relative permittivity  $\varepsilon_r \le 1,4$ )
- 7 device under test
- 8 input/output leads

ISO/FDIS 11452-3

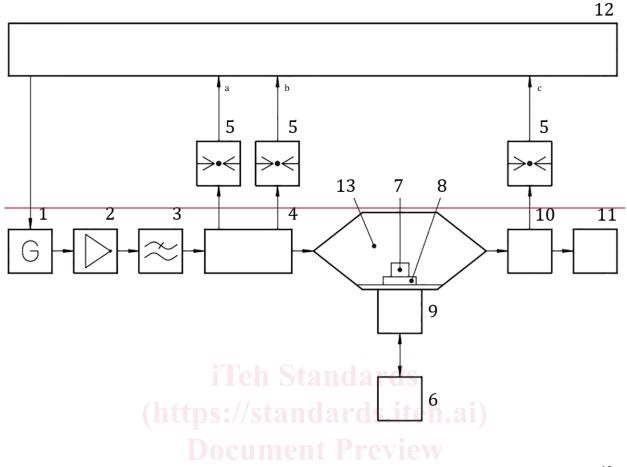
https://standards.iteh.ai/catalog/standards/Figure 1 — TEM cell<sup>9</sup>dd-a0b2-d081ef66b8de/iso-fdis-11452-3

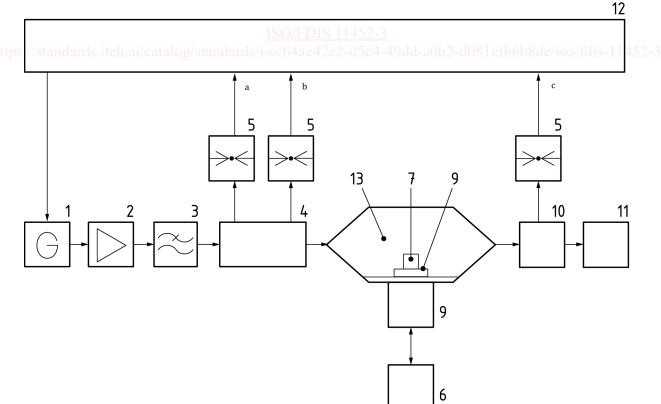
#### 5.2 Instrumentation

Figure 2 Figure 2 shows an example of a TEM cell test set-up. The TEM cell has high resonances in the region greater than the recommended upper frequency limit.

A low pass filter with an attenuation of at least 60 dB at frequencies above 1,5 times the cut-off frequency of the TEM cell may be installed (e.g. 200 MHz TEM cell: 60 dB for frequencies above 300 MHz) to avoid resonances.

#### Example of installation of low pass filter is given in Annex C





Key

#### ISO/TC22/SC32/WG3FDIS 11452-3:2024(en)

low pass filters/connector panel 1 signal generator 2 broadband amplifier 10 coupler 3 low pass filter (optional) 11 high power load (50  $\Omega$ ) 4 dual-directional coupler (30 dB decoupling ratio 12 controller minimum) 13 TEM cell RF-power meter 5  $P_{\text{forward}}$  (forward power). 6 peripheral  $P_{\text{reflected}}$  (reflected power). 7 device under test *P*<sub>output</sub> (output power). 8 dielectric support

Figure 2 — Example TEM cell configuration

#### 5.3 Test set-up

#### 5.3.1 General

In order to maintain the homogeneous field in the TEM cell and obtain reproducible measurement results, the device under test shall be no larger than one-sixth of the cell (inside) height, b (see Figure 3 Figure 3 and Figure A.1). The device under test should be placed in the centre of the cell on a dielectric equipment support.

The device under test and the wiring harness may be positioned in either of two arrangements, depending on whether the exposure of the device under test and the wiring harness (see 5.3.25.3.2) or that of the device alone (see 5.3.35.3.3) is being tested.

An alternative test set-up without low pass filter is presented in Annex D.

#### 5.3.2 Exposure of device under test and wiring harness (for major field coupling to the harness)

The height of the dielectric support is one-sixth of cell height *b* (see Figure 3Figure 3).]. In order to obtain reproducible measurement results, the device under test, together with its wiring harness or printed circuit board, shall be placed in the same position in the TEM cell for each measurement. In addition to the direct RF-field coupling to the device under test, the use of an unshielded harness or printed circuit board will result in a common mode electrical field coupling and a differential mode magnetic field coupling, depending on the inclination and the width of the harness or circuit board.